

Ultrafast filling of an electronic pseudogap in $[\text{LaS}]_{1.2}\text{VS}_2$

Véronique Brouet, J. Mauchain, E. Papalazarou, P.-H. Lin, M. Marsi
Laboratoire de Physique des Solides d'Orsay



A. Taleb-Ibrahimi, P. Le Fèvre, F. Bertran
CASSIOPEE beamline, France
SOLEIL synchrotron

L. Cario, E. Janod, B. Corraze
IMN Nantes, France
Sample synthesis

Luca Perfetti, Jérôme Faure
Ecole Polytechnique, Palaiseau, France
FemtoARPES

Vinh Ta Phuoc
Université Tours, France
Optical measurements

Outline

[LaS]_{1,2}VS₂ : a « strange » insulator

⇒ Resistive switching under applied electric pulses

ARPES investigation of the electronic structure

⇒ A very strong temperature dependence of the Fermi level « pseudogap »

Manipulating the pseudogap by pump-probe experiments

⇒ Ultrafast filling of the pseudogap

⇒ Evidence for very strong electron-phonon coupling

[LaS]_{1,2}VS₂ appears to be at the frontier between cluster and solid behaviors

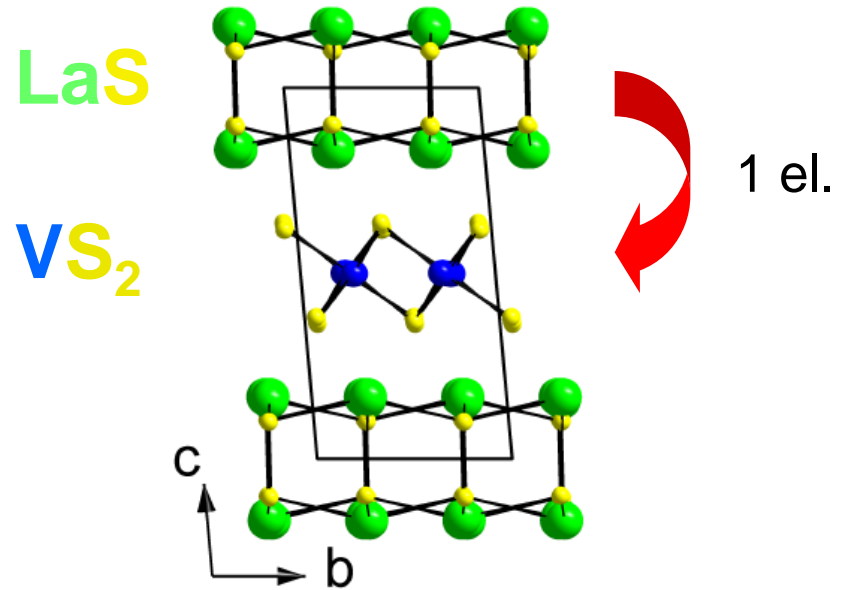
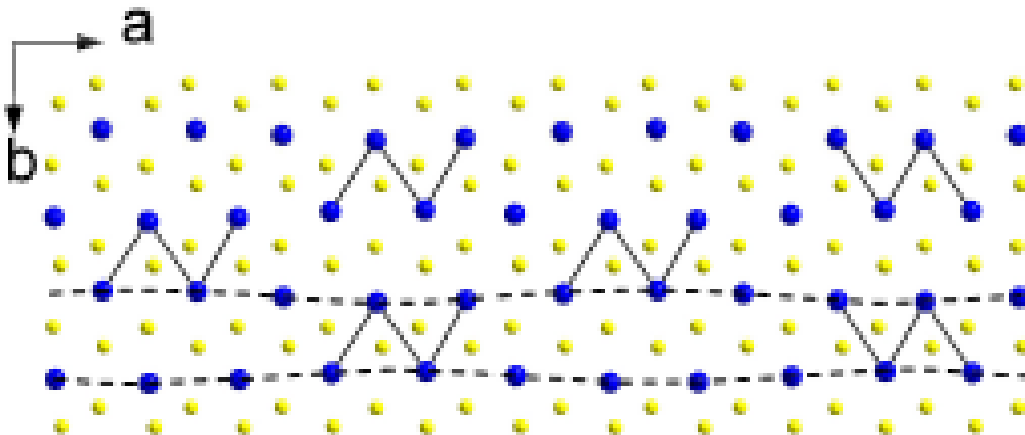
[LaS]_{1.2}VS₂ : a « misfit » structure

LaS and VS₂ are incommensurate along a.

=> approximate supercell :

$$3 \cdot a_{\text{LaS}} = 5 \cdot a_{\text{VS}_2} = 17 \text{ \AA}$$

Distorted triangular V planes



Modulation of V position with :

$$q = \frac{a_{\text{VS}_2}}{a_{\text{LaS}}} a_{\text{VS}_2}^* = 1,1 \text{ \AA}^{-1}$$

$$\Rightarrow \text{V-V (min)} = 2,92 \text{ \AA}$$

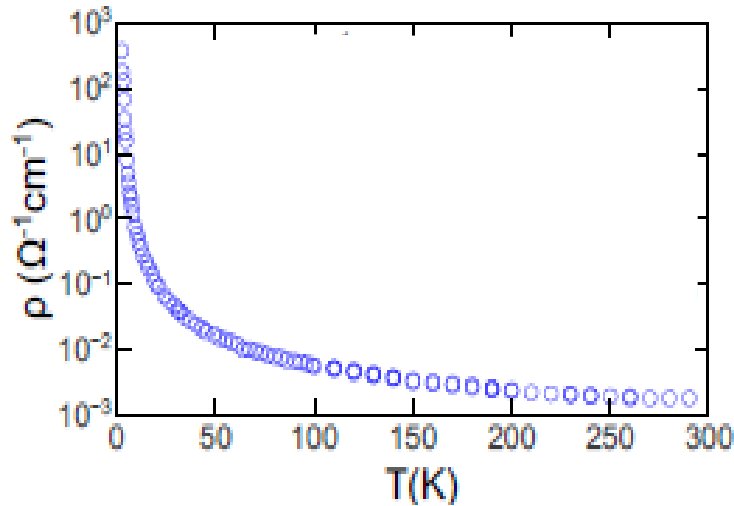
$$\text{V-V (max)} = 3,73 \text{ \AA}$$

A « strange » insulator ?

- 2.2 electrons in the V 3d t_{2g} orbitals

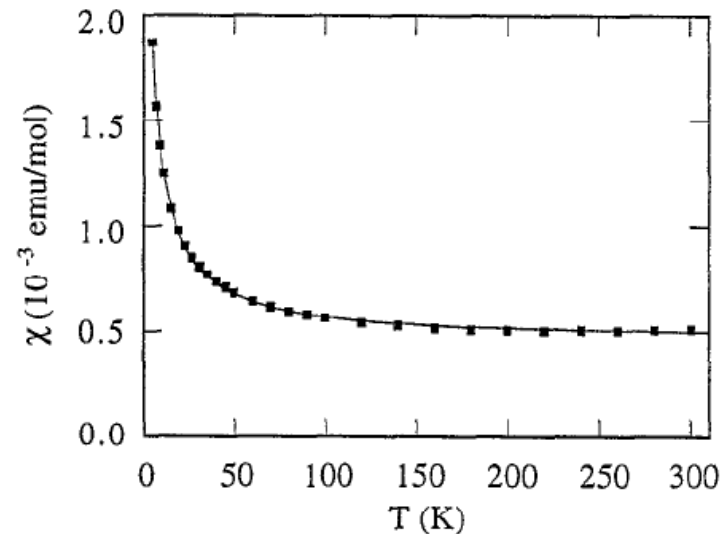
Resistivity

~ semiconducting-like ?



Susceptibility

~ Pauli-like ?

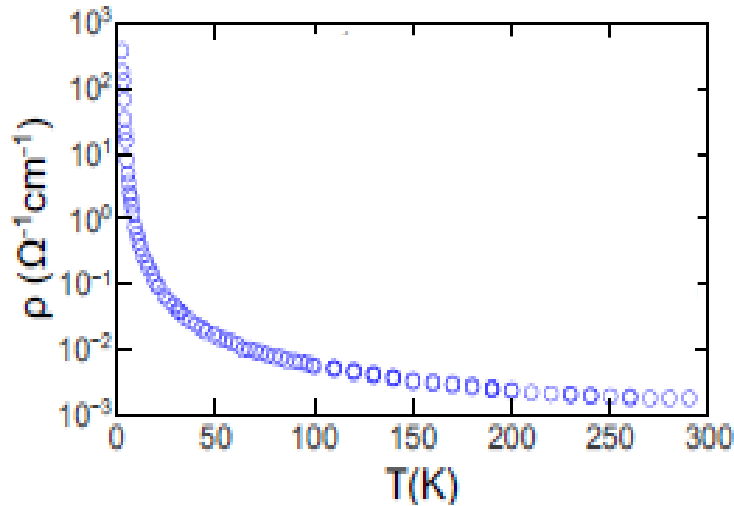


A « strange » insulator ?

- 2.2 electrons in the V 3d t_{2g} orbitals

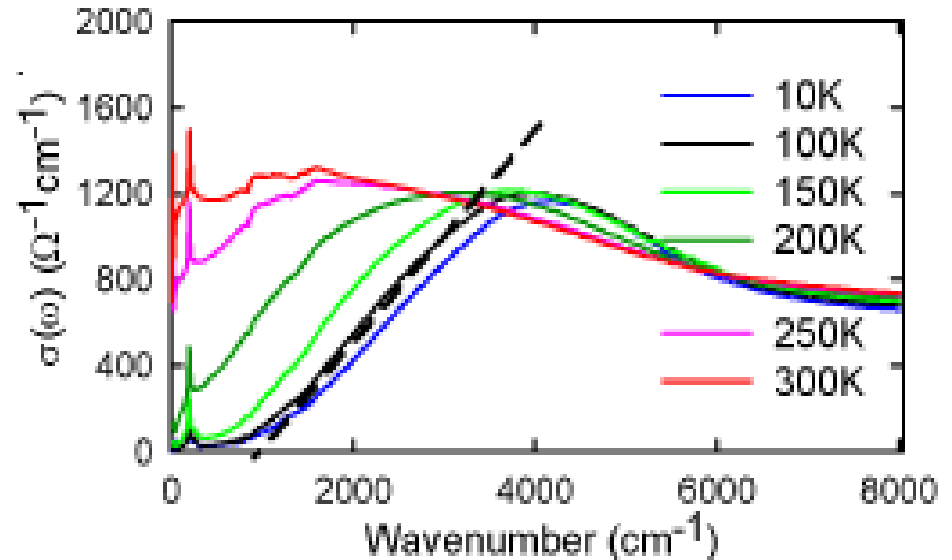
Resistivity

~ semiconducting-like ?



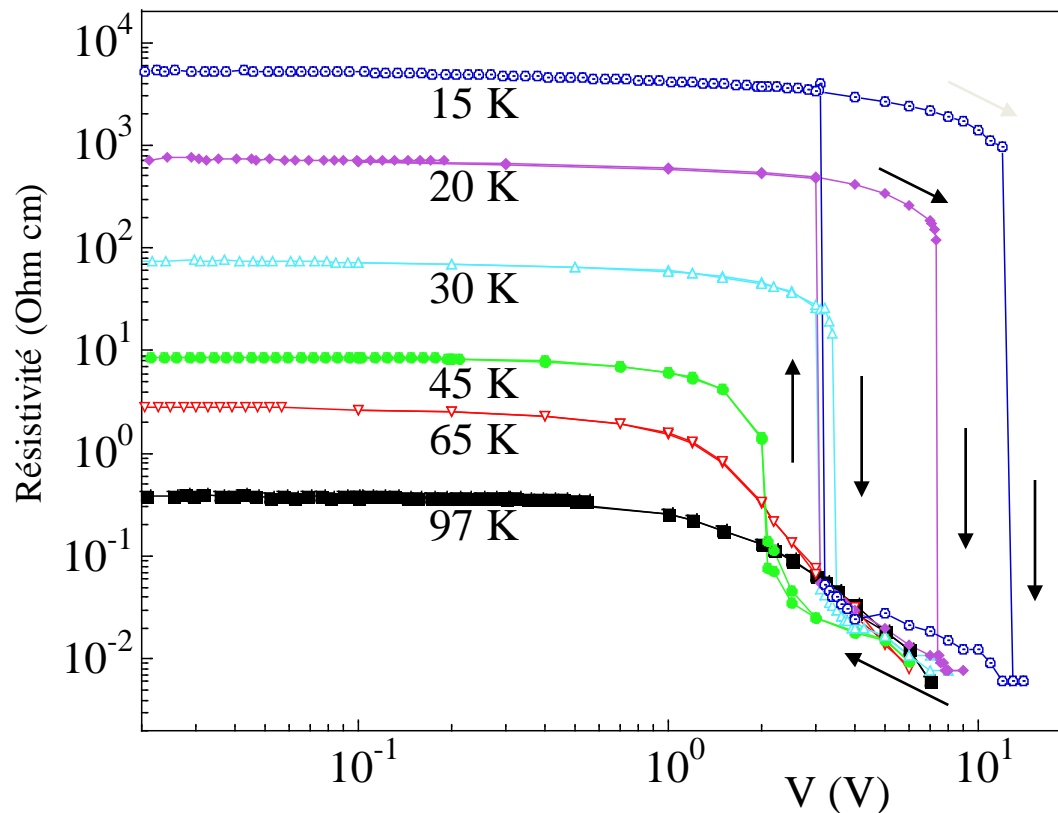
Optical conductivity

Unexpectedly strong T dependence !

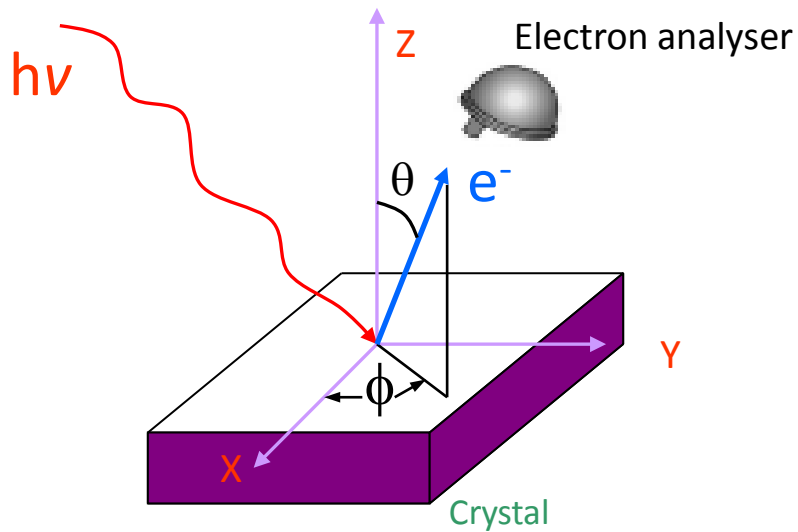


Resistive switching under applied electric pulses

Resistivity can change up by 5 order of magnitudes !

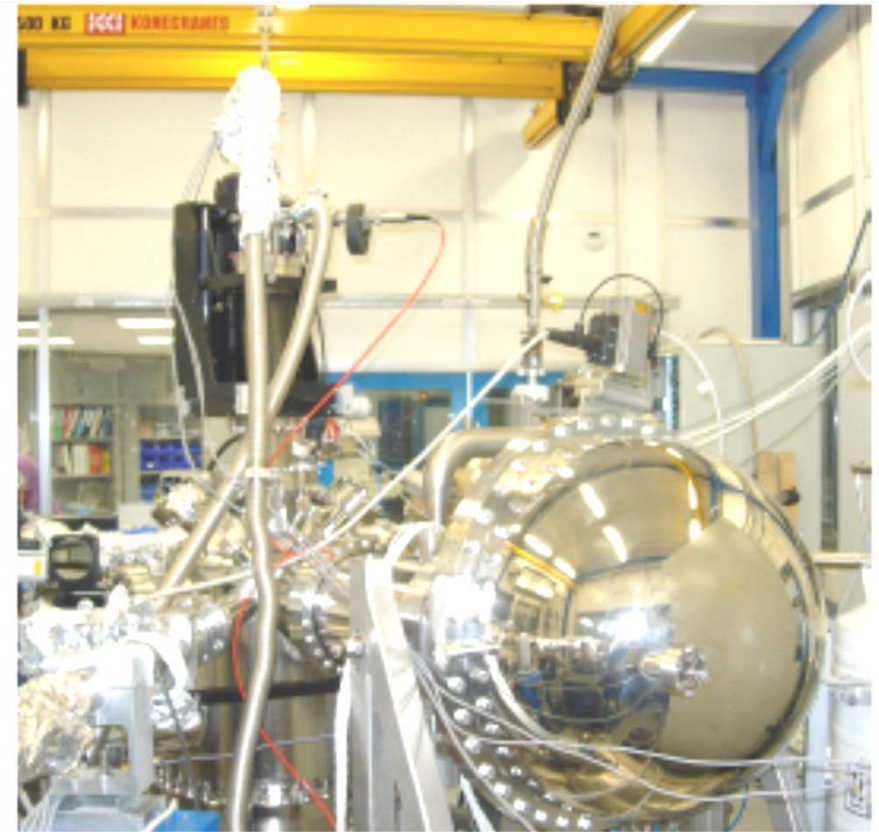


ARPES view of the electronic structure



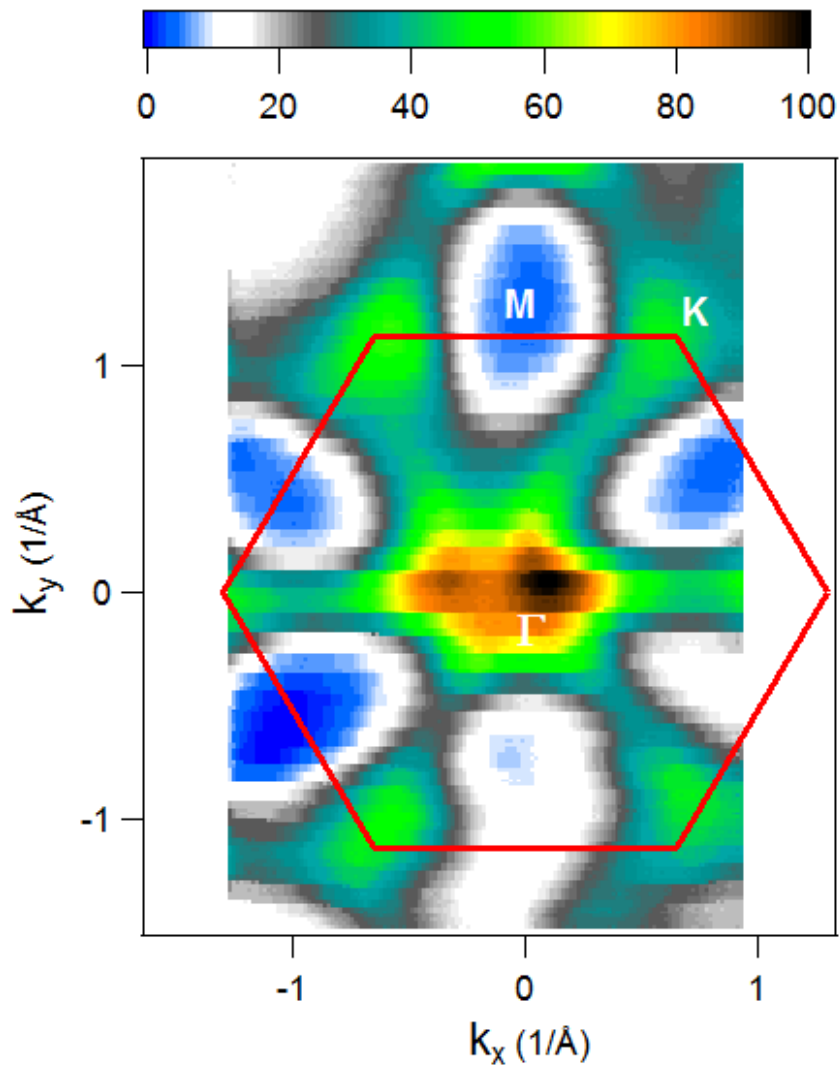
$$E_{kin} = h\nu - W - |E_B|$$

$$\hbar\mathbf{k}_{\parallel} = \sqrt{2mE_{kin}} \sin \theta$$

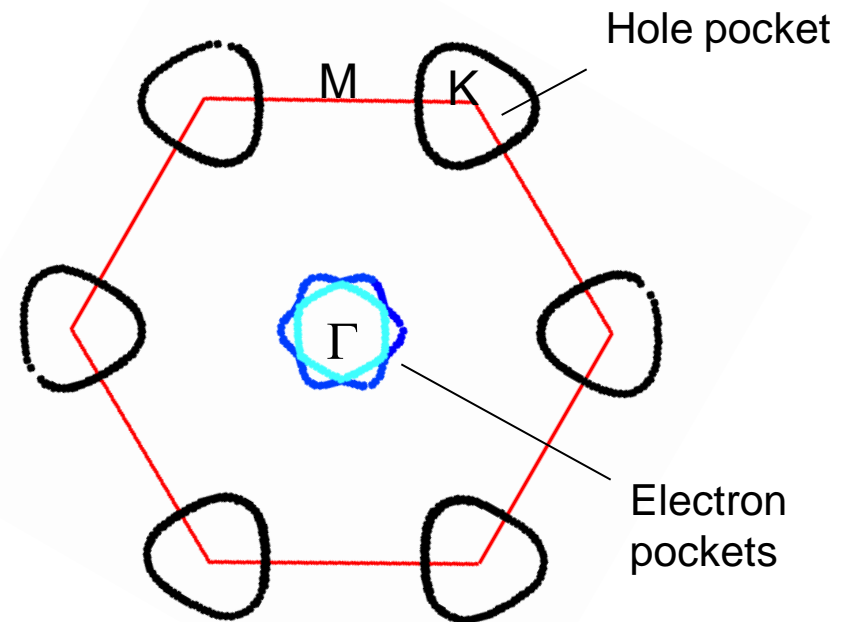


CASSIOPEE beamline, SOLEIL synchrotron
=> 10-1000eV
=> high energy and angular resolution

Fermi Surface (300K, 96eV)

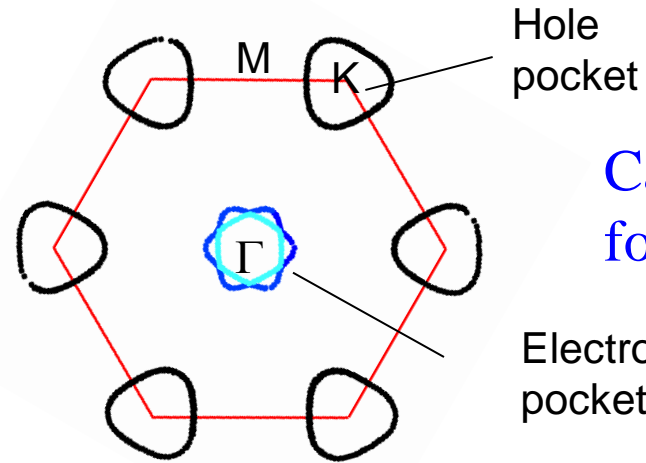
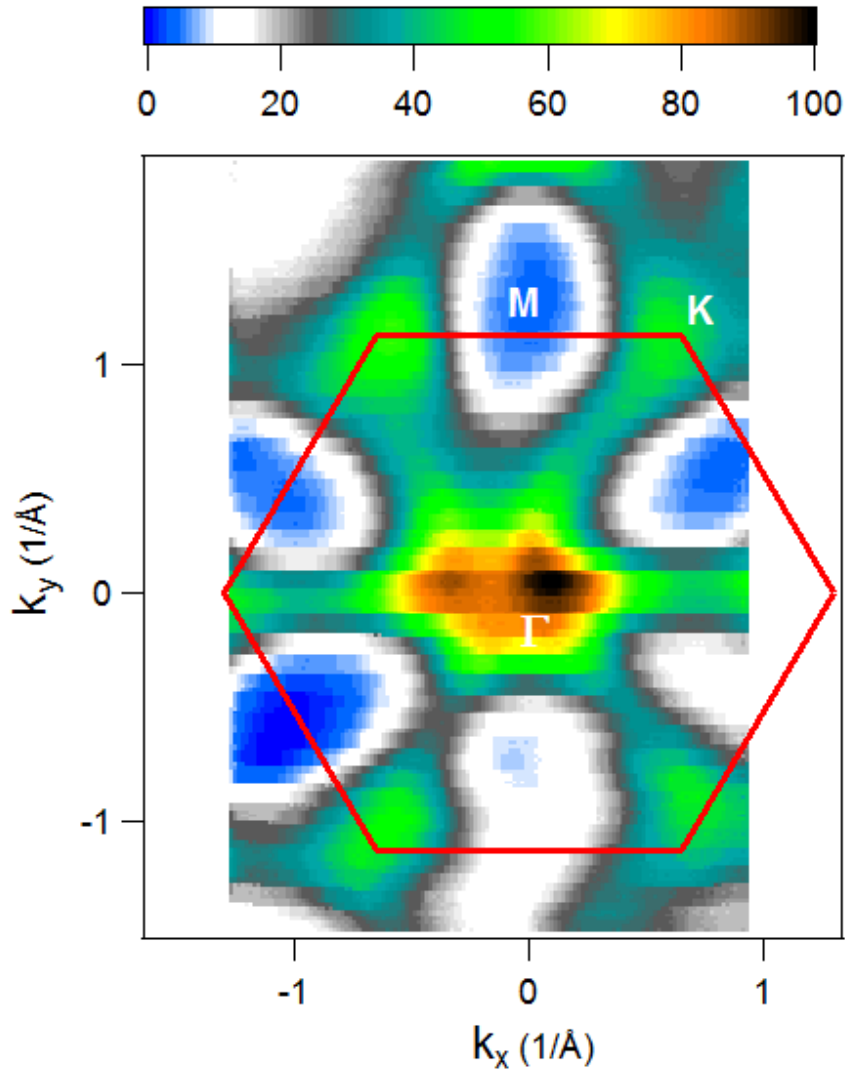


Calculated FS in LiVS_2 (d^2)

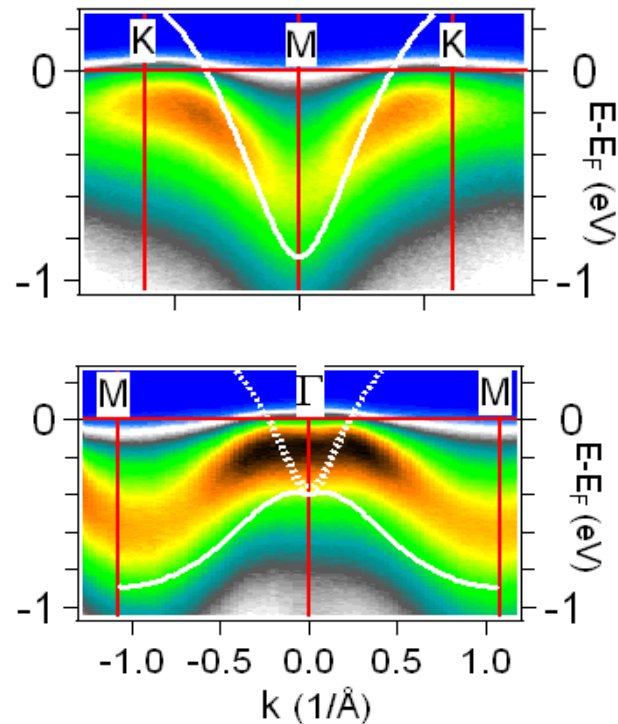


=> 6-fold symmetry expected for a triangular lattice

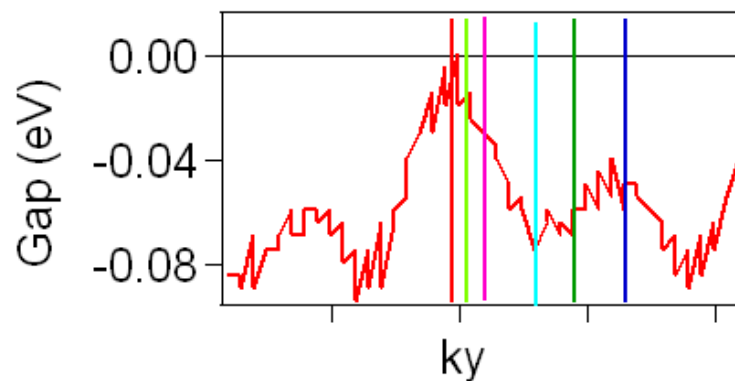
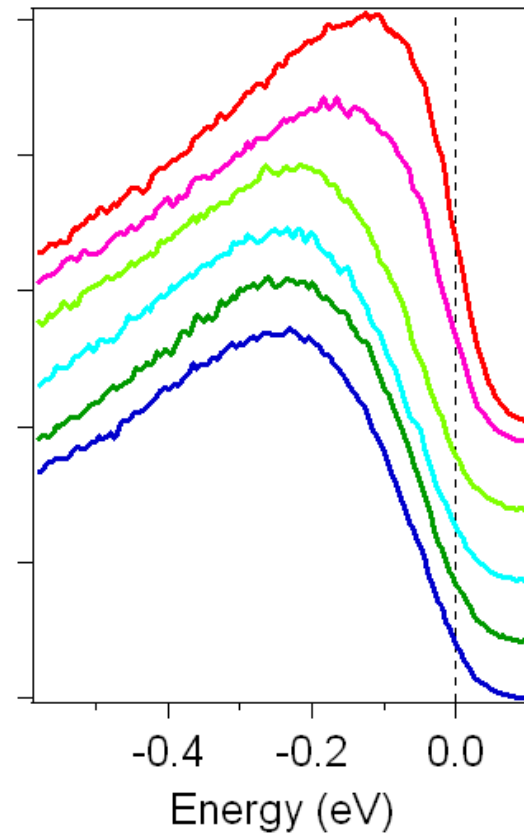
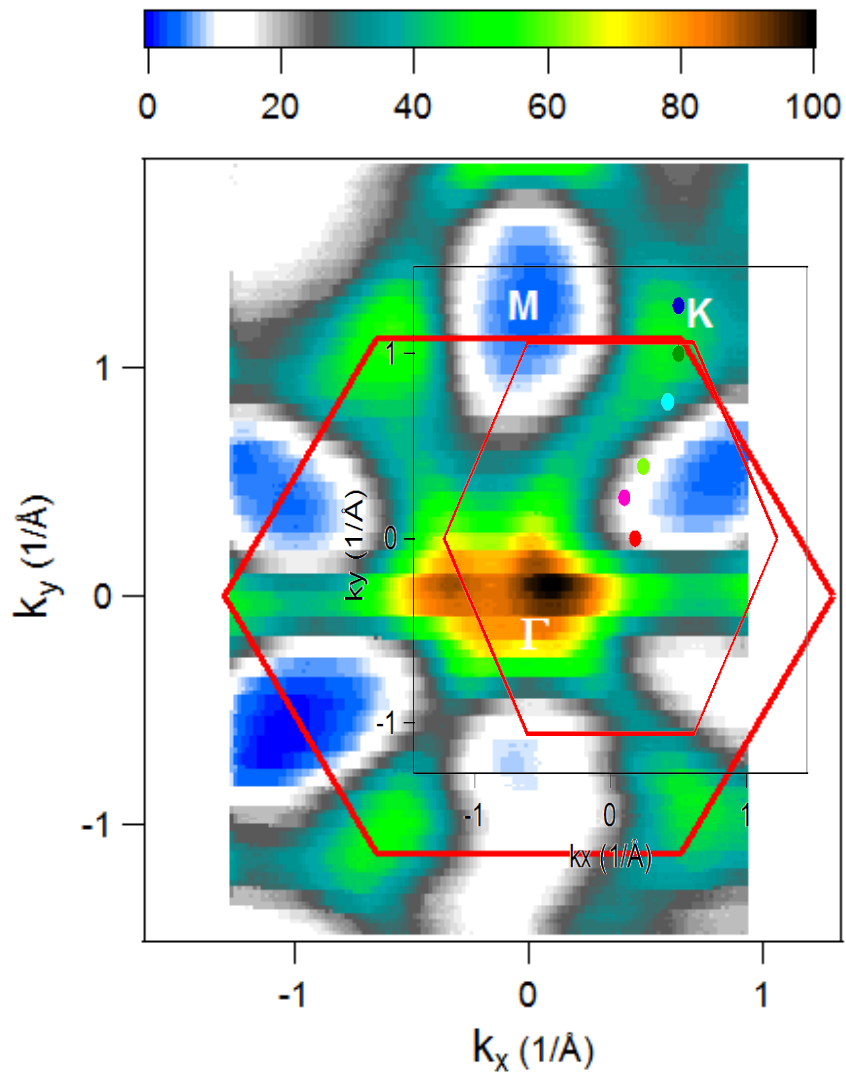
Fermi Surface & band structure



Calculation
for LiVS_2

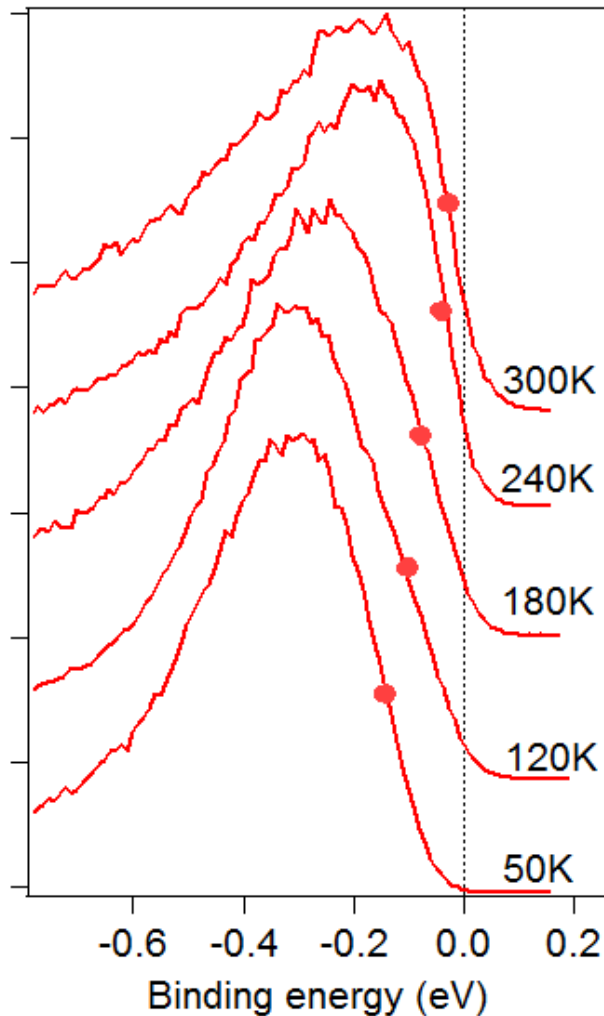


Pseudogaps along the FS (300K)

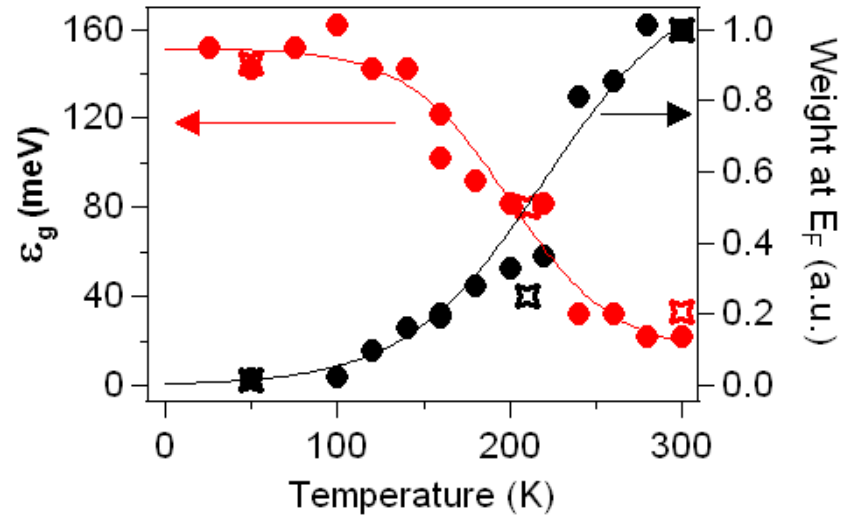


Evolution with temperature (at Γ)

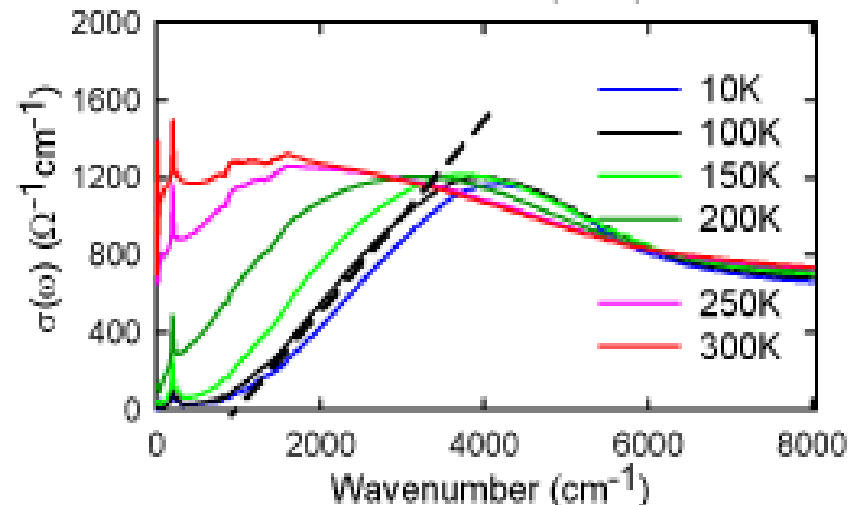
ARPES spectra as a function of T



Gaps and spectral weight at E_F



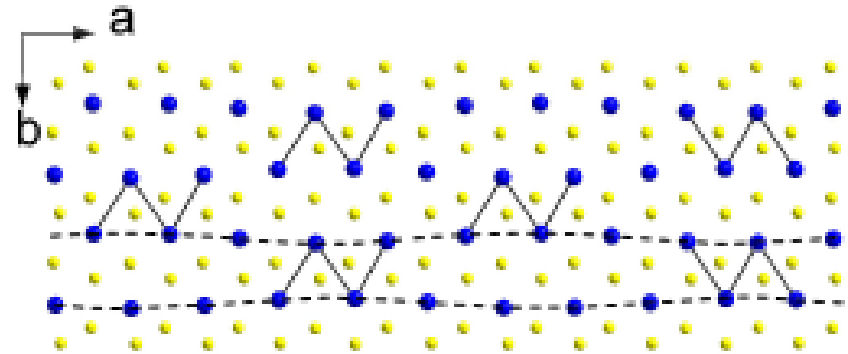
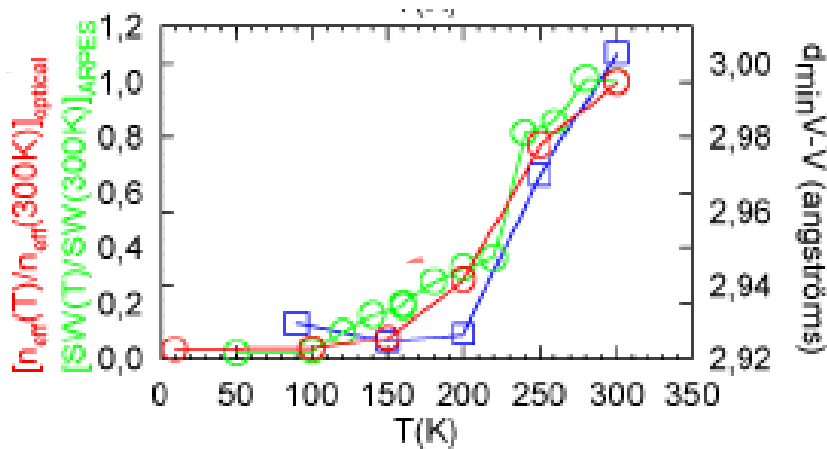
Optical conductivity



First angle integrated study :
Ino, Fujimori et al., PRB 2004

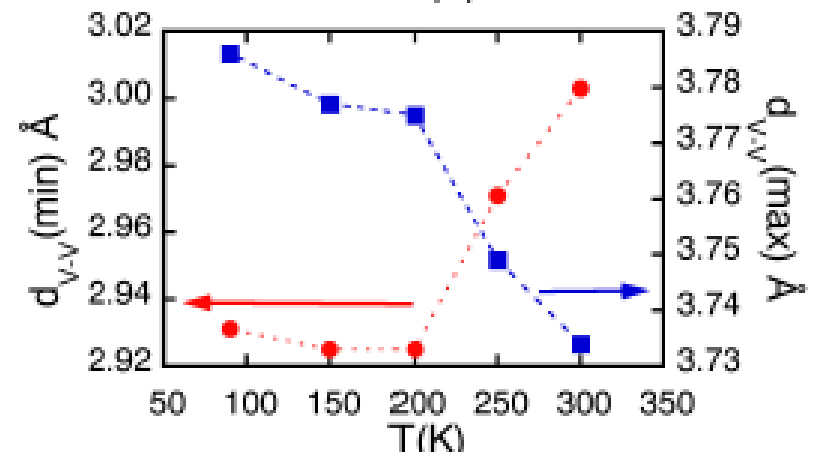
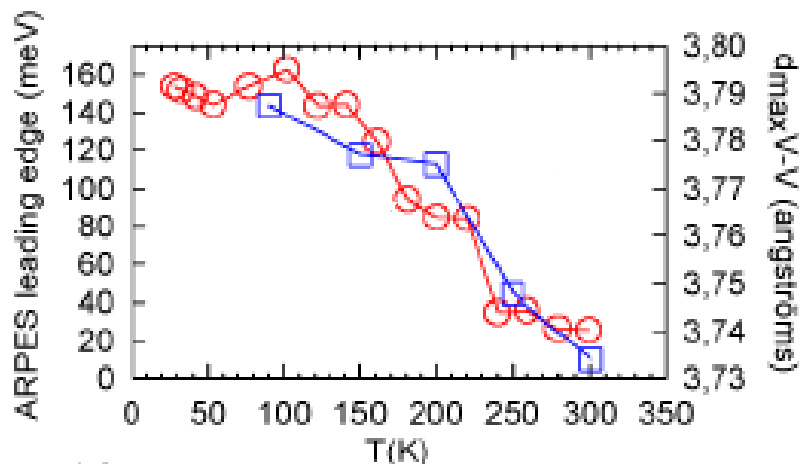
Direct connection between $n(E_F)$ and structure

ARPES and optic spectral weight scale with the distortion



The modulation amplitude increases with decreasing T

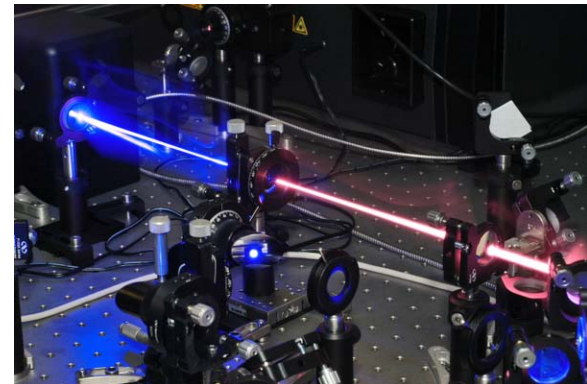
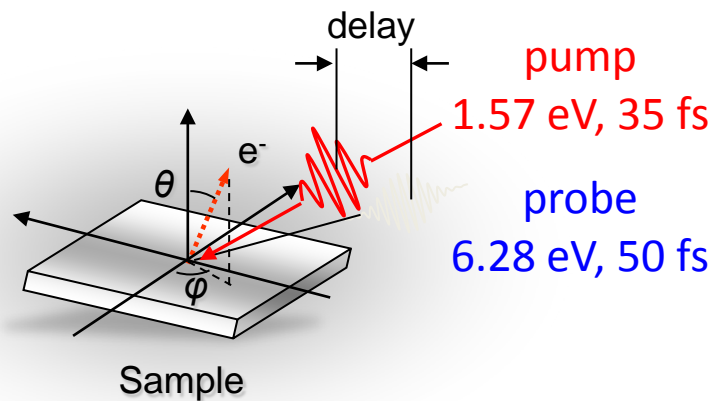
ARPES pseudogap scales with the distortion



Probing the dynamic of the pseudogap formation

How are structural and electronic degrees of freedom linked in this system ?

FemtoARPES setup

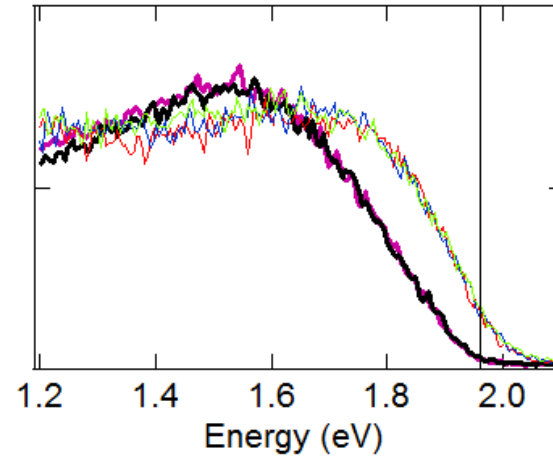
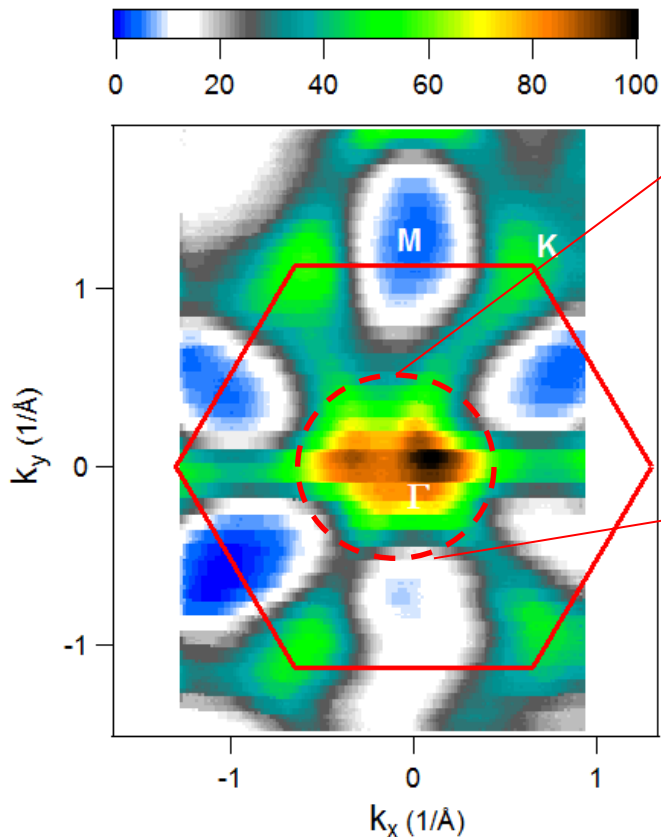


J. Faure *et al.*, *Rev. Sci. Instrum.*, 2012

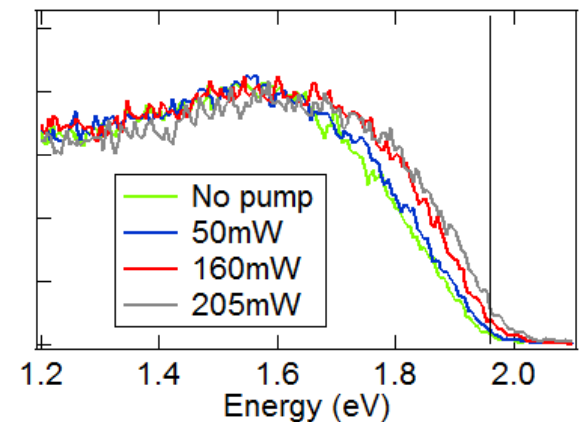
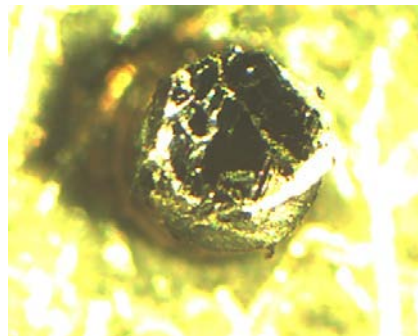
Laser ARPES of $[\text{LaS}]_{1.2}\text{VS}_2$ (6.28eV)

Opening of the pseudogap between
300 and 40 K observed at 6eV

FS measured at 100eV



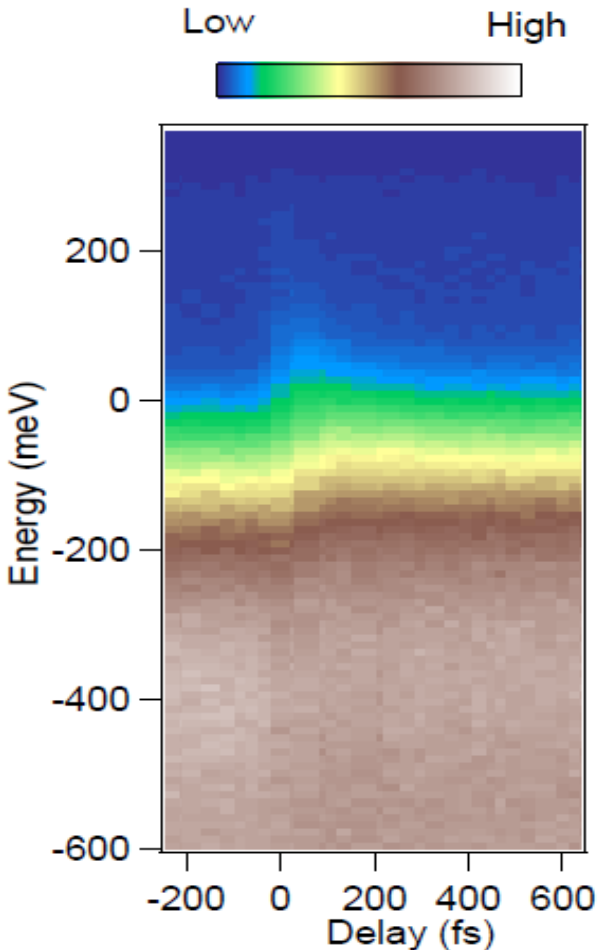
Heating due to laser pumping



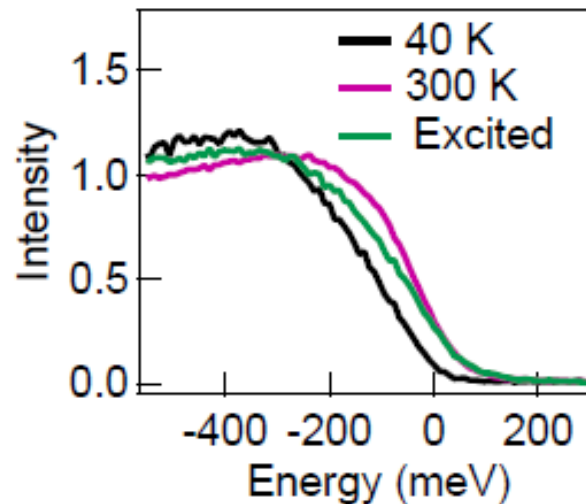
=> Cut down repetition rate

Ultrafast filling of the pseudogap

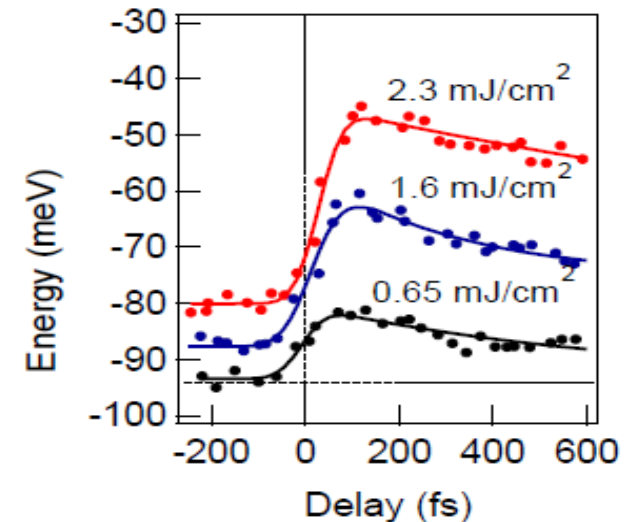
Sample at 40K excited by laser pulse of 2.3 mJ/cm^2 fluence



Excited spectra (green) compared to high and low T



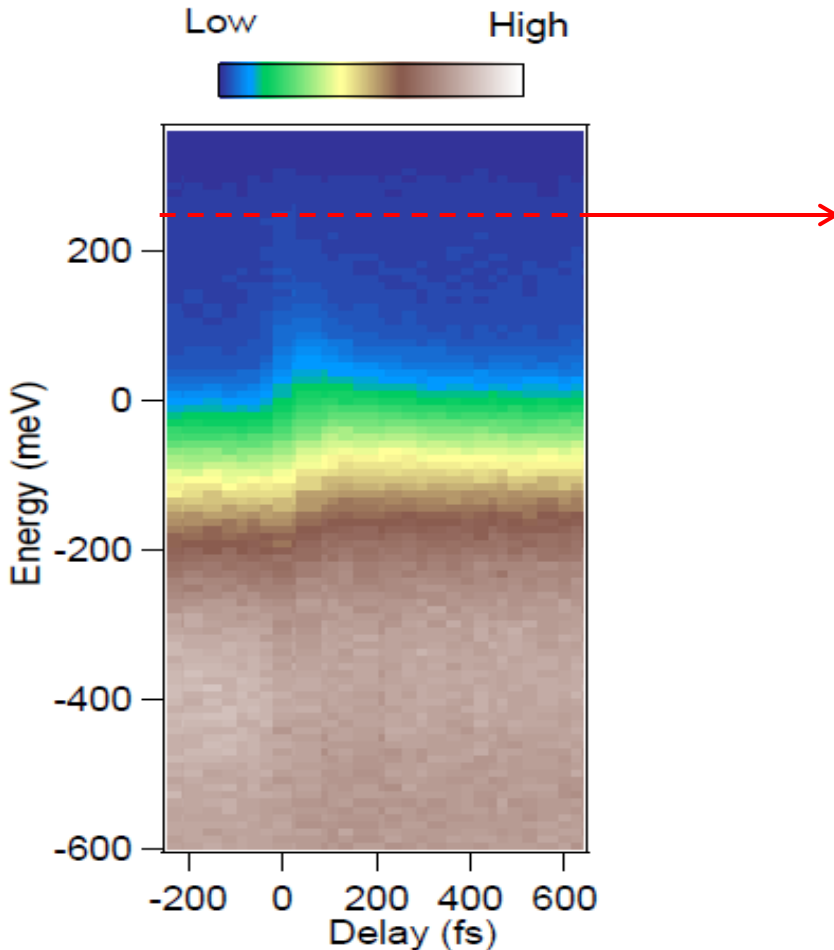
Leading edge vs delay



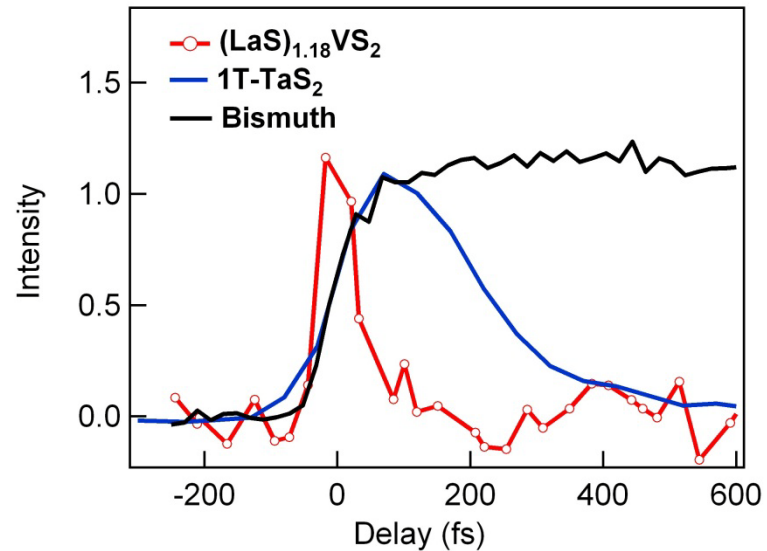
The pseudogap fills up in less than 80fs, close to the experiment temporal resolution

Ultrafast filling of the pseudogap

Sample at 40K excited by laser pulse of 2.3 mJ/cm^2 fluence



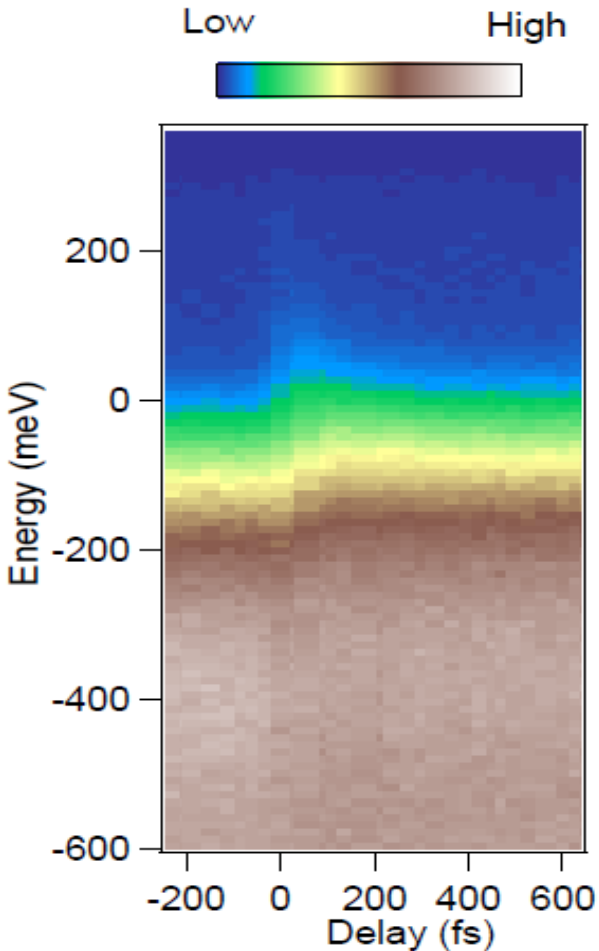
Comparison of hot electron decay rate in different systems



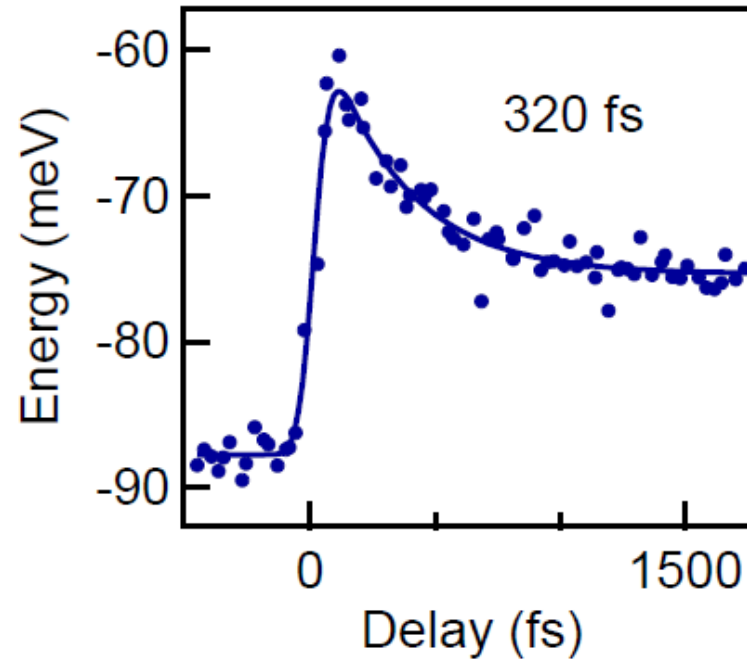
Hot electrons release their energy to phonon modes in less than 80fs.
=> very strong electron-phonon coupling

Ultrafast filling of the pseudogap

Sample at 40K excited by laser pulse of 2.3 mJ/cm^2 fluence

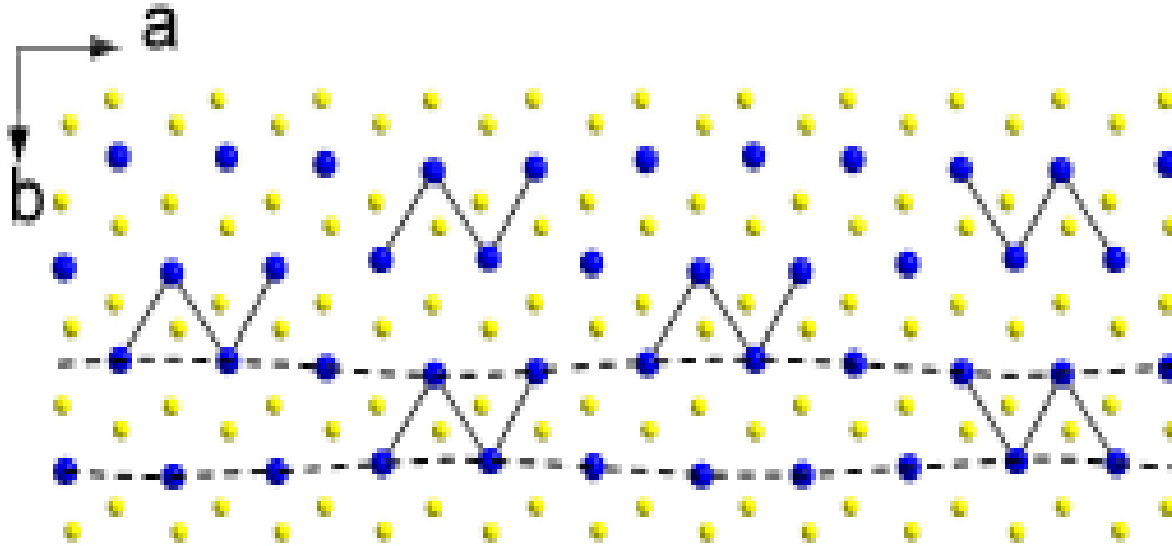


Recovery of the pseudogap



After closing the gap, the system is still far from thermal equilibrium.

Why is $[\text{LaS}]_{1.2}\text{VS}_2$ insulating ?

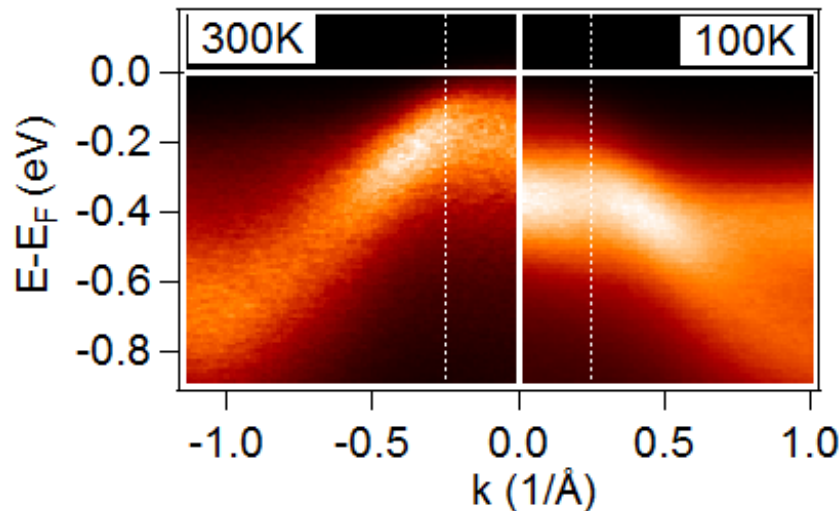
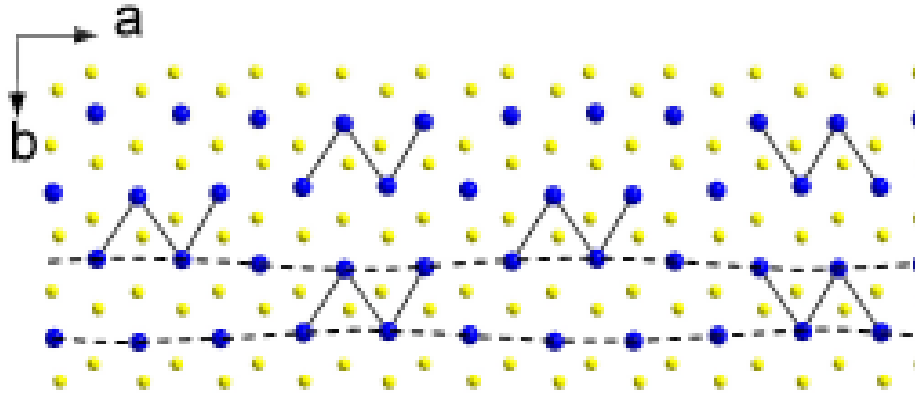


2.2 el. / V

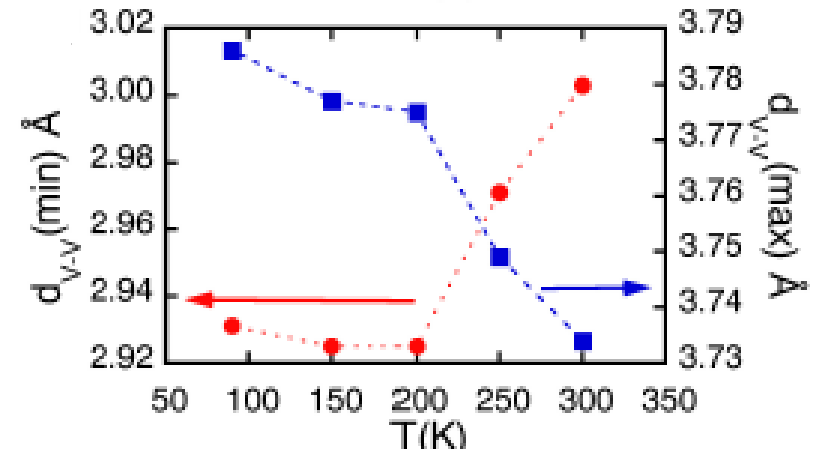
- Band gap
*Incommensurate structure : it's hard to make a band insulator !
Why such a fast relaxation ?*
- Mott, electronic correlations...
Not close to half-filling, no strong renormalization => unlikely
- Disorder
Clear dispersion in ARPES, clear modulation in x-ray => unlikely

Change of electronic structure with T

There is no gap opening at low T but a complete change of electronic structure



Modulation amplitude vs T



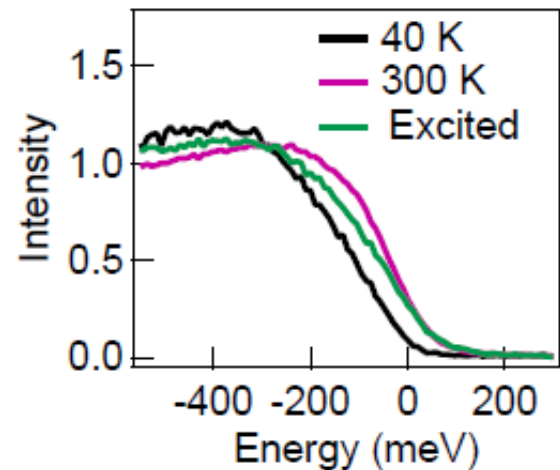
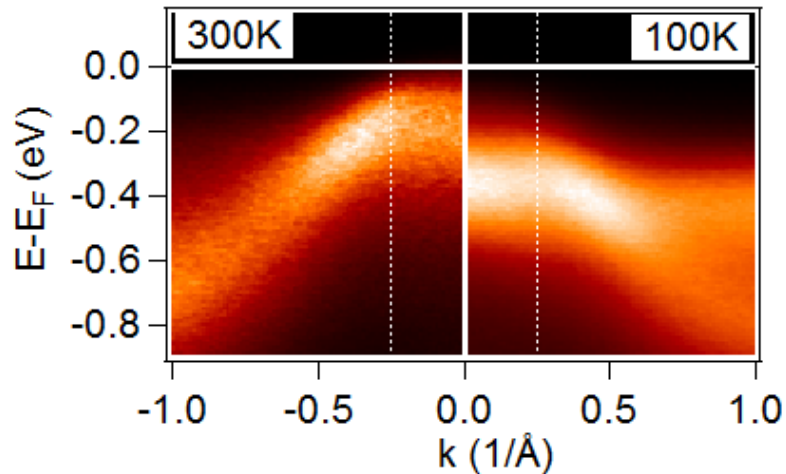
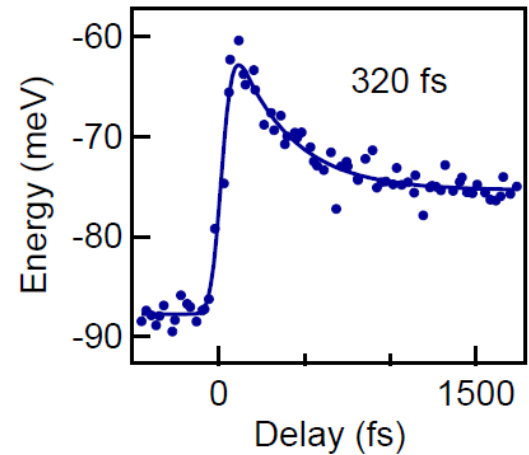
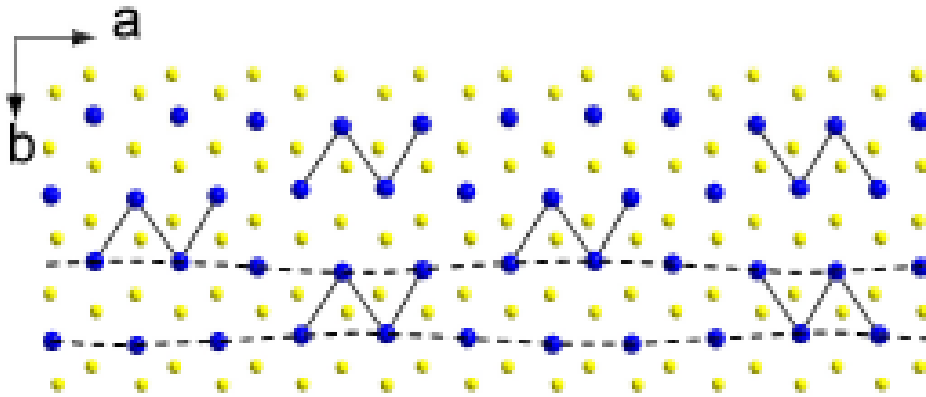
⇒ The distortion brings atoms close to chemical bonding in V clusters

⇒ Very strong electron-phonon coupling !

Strong coupling between distortion and electronic properties

⇒ No collective excitation

⇒ Filling of the gap by local and incoherent excitations



On the origin of charge-density waves in select layered transition-metal dichalcogenides

Table 1. Qualitative comparison of weak-coupling and strong-coupling CDWs.

	Weak-coupling CDW	Strong-coupling CDW
PLD/CDW amplitude	Small	Large
Energy gap	Small ($\Delta/E_F \ll 1$)	Large ($\Delta/E_F \lesssim 1$)
Coherence length	Large ($\xi/a \gg 1$)	Small ($\xi/a \lesssim 1$)
Electronic energy gain	Arising mostly near k_F ($\propto \Delta^2 \ln \Delta$)	Spread over Brillouin zone ($\propto \Delta$)
CDW periodicity w.r.t. original lattice	Incommensurate ($\lambda_0 = \pi/k_F$)	Tends to be commensurate
Thermal disordering	Due to electronic entropy	Due to lattice entropy
Electron-hole pairing above T_0	No	Yes, but pairs are incoherent
Qualitative picture	Fermi surface instability	Local chemical bonding

K. Rossnagel et al., J. Phys Cond Mat 2011

Conclusion :

nature of the instability in $[\text{LaS}]_{1.2}\text{VS}_2$?

« purely
electronic »

coupled

« purely
structural »

Origin of the instability

Mott insulator

Charge Density Waves

Band insulator

Excitonic insulator

$[\text{LaS}]_{1.2}\text{VS}_2$?

weak

strong

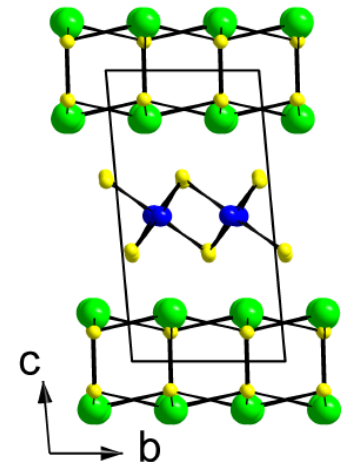
collective

el-ph coupling

molecular

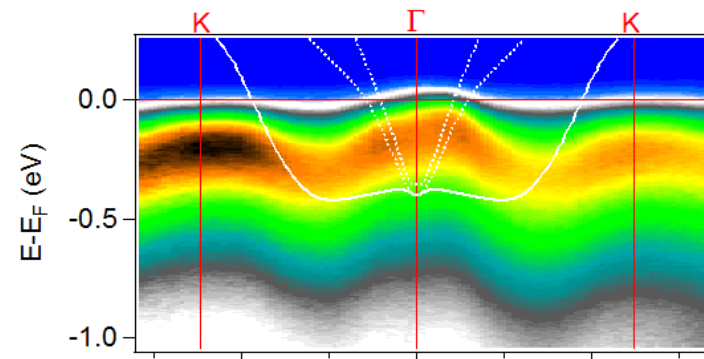
⇒ Such « hidden » chemical bonding could play a role in many « CDW » systems or valence bond solids (LiVS_2)

⇒ High sensitivity to perturbations : resistive switching





GK dipersion



Band structure for $a=3.4\text{\AA}$ and 3.5\AA

